

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Atty. Docket No. 04329.2222		Serial No.	Not Yet Assigned		
Applicant Kouji MATSUO et al.					
Filing Date January 28, 2000		Group			
U.S. PATENT DOCUMENTS					
Examiner Initial*	Document Number	Date	Name	Class	Sub Class
FOREIGN PATENT DOCUMENTS					
	Document Number	Date	Country	Class	Sub Class
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
<i>CW</i>	Wittner, M. et al. "Oxidation Kinetics of TiN Thin Films", J. Appl. Phys., Vol. 52, pp. 6659-6664, November (1981).				
<i>SM</i>	Matsuo, K. et al., "Reliable High-k TiO ₂ Gate Insulator Formed by Ultrathin TiN Deposition and Low Temperature Oxidation", Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials pp. 164-165, (1999).				
Examiner <i>J</i>	Date Considered 10/16/01				
*Examiner:	Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.				
Form PTO 1449			Patent and Trademark Office - U.S. Department of Commerce		

11-5514 S.
 09/492780
 01/2001